



2814

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Anthony *et al.*

Docket:

TI-24953

Appl. No.: 09/116,138

Examiner:

A. Mai

Filed: 07/15/98

Art Unit:

2814

For: High Permittivity Silicate Gate Dielectric

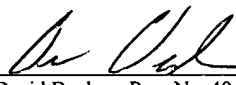
#21/D
8/22/01
SunderREPLY PURSUANT TO 37 C.F.R. § 1.111

August 9, 2001

Ass't Commissioner for Patents
Washington, DC 20231

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, DC 20231 on August 9, 2001.


David Denker Reg. No. 40,987

Examiner:

In response to the Office Action dated May 9, 2001, please amend the above-identified patent application as follows:

IN THE SPECIFICATION08/21/2001 SSURLES 00090001 400660 09/116138
A. Page 1, please replace the second paragraph with:01 FC:103 -- 540116138
Dr This invention is related to concurrently filed applications Serial No. 09/115,855, pending and Serial No. 09/115,856, abandoned, which are incorporated herein by reference.--IN THE CLAIMS

- B. Please cancel claims 41 - 45. ✓
- C. Please add claims 46 - 80 as shown below.
- D. Please amend claims 4 and 40 as shown below.

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D2 4. (amended) The method of claim 2, wherein the oxidizing step comprises simultaneous exposure of the layer of a silicide of the first metal to an oxidizing gas and a reducing gas.

D3 40. (amended) An integrated circuit made by the method of claim 26.